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Advanced Etch Technology for Nanopatterning IX

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Contents

v *Authors*
vii *Conference Committee*

MATERIALS AND ETCH INTEGRATION

11329 05 **Novel etch technologies utilizing atomic layer process for advanced patterning (Invited Paper)**
[11329-5]

COMPUTATIONAL PATTERNING AND PATTERNING PROCESS CONTROL

11329 09 **Reduction of systematic defects with machine learning from design to fab (Invited Paper)**
[11329-9]

11329 0C **Optimal etch recipe prediction for 3D NAND structures** [11329-12]

ATOMIC LAYER ETCHING AND NOVEL PLASMA TECHNIQUES

11329 0G **Cycling of implantation step and remote plasma process step for nitride spacer etching applications** [11329-16]

EUV PATTERNING AND ETCH: JOINT SESSION WITH CONFERENCES 11323 AND 11329

11329 0H **Simulation of photoresist defect transfer through subsequent patterning processes** [11329-18]

11329 0I **Low damage etching by Inductively Coupled Plasma Reactive Ion Etch (ICP-RIE) and Atomic Layer Etching (ALE) of III-V materials to enable next generation device performance** [11329-17]

ADVANCED PATTERNING INTEGRATION

11329 0O **FEOL dry etch process challenges of ultimate FinFET scaling and next generation device architectures beyond N3 (Invited Paper)** [11329-24]

11329 0S **Hydrocarbon layer formation and removal studies on SiN films etched in halogen/hydrofluorocarbon plasmas** [11329-28]

11329 0T **Improvement of self-aligned dual patterning using spin-on-carbon mandrel** [11329-29]

POSTER SESSION

- 11329 0V **Cleaning chamber walls after ITO plasma etching process** [11329-30]
- 11329 0X **Machine learning assistant technology to facilitate Fin and 3D memory measurements on SEM and TEM images** [11329-32]
- 11329 0Z **Accelerated optimization of multilayer trench etches using model-based experimental design** [11329-34]
- 11329 10 **Intra-field etch induced overlay penalties** [11329-35]